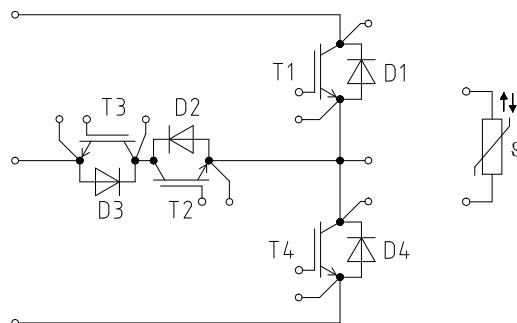
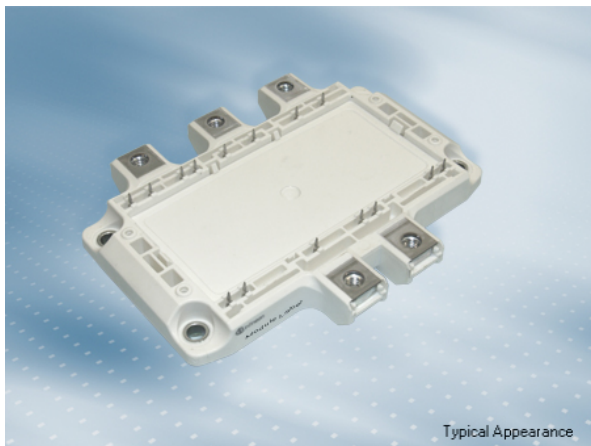


EconoPACK™4 模块 采用第二类中点钳位拓扑 (NPC2) 带有pressfit压接管脚和温度检测NTC
EconoPACK™4 module with active "Neutral Point Clamp 2" topology and PressFIT / NTC

初步数据 / Preliminary Data



$V_{CES} = 1200V$
 $I_{C\ nom} = 400A / I_{CRM} = 800A$

典型应用

- 太阳能应用
- UPS系统

Typical Applications

- Solar Applications
- UPS Systems

电气特性

- 提高工作结温 $T_{vj\ op}$
- 低开关损耗
- 低 V_{CEsat}
- 沟槽栅IGBT4
- $T_{vj\ op} = 150^{\circ}C$
- V_{CEsat} 带正温度系数

Electrical Features

- Extended Operation Temperature $T_{vj\ op}$
- Low Switching Losses
- Low V_{CEsat}
- Trench IGBT 4
- $T_{vj\ op} = 150^{\circ}C$
- V_{CEsat} with positive Temperature Coefficient

机械特性

- 绝缘的基板
- 紧凑型设计
- PressFIT 压接技术
- 标封装

Mechanical Features

- Isolated Base Plate
- Compact design
- PressFIT Contact Technology
- Standard Housing

Module Label Code

Barcode Code 128



DMX - Code



Content of the Code

Digit

Module Serial Number	1 - 5
Module Material Number	6 - 11
Production Order Number	12 - 19
Datecode (Production Year)	20 - 21
Datecode (Production Week)	22 - 23

prepared by: MK	date of publication: 2013-11-11	
approved by: MK	revision: 2.0	UL approved (E83335)



初步数据
Preliminary Data

IGBT, T1 / T4 / IGBT, T1 / T4

最大额定值 / Maximum Rated Values

集电极 - 发射极电压 Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	1200	V
连续集电极直流电流 Continuous DC collector current	$T_C = 100^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	$I_{C\text{nom}}$ I_C	400 600	A A
集电极重复峰值电流 Repetitive peak collector current	$t_P = 1\text{ ms}$	I_{CRM}	800	A
总功率损耗 Total power dissipation	$T_C = 25^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	P_{tot}	2150	W
栅极 - 发射极峰值电压 Gate-emitter peak voltage		V_{GES}	+/-20	V

特征值 / Characteristic Values

			min.	typ.	max.	
集电极 - 发射极饱和电压 Collector-emitter saturation voltage	$I_C = 400\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 400\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 400\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{sat}}$	1,75 2,05 2,10	2,15	V V V
栅极阈值电压 Gate threshold voltage	$I_C = 15,0\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		V_{GEth}	5,2	5,8	6,4 V
栅极电荷 Gate charge	$V_{GE} = -15\text{ V} \dots +15\text{ V}$		Q_G	3,30		μC
内部栅极电阻 Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		R_{Gint}	1,8		Ω
输入电容 Input capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{ies}	25,0		nF
反向传输电容 Reverse transfer capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{res}	1,35		nF
集电极-发射极截止电流 Collector-emitter cut-off current	$V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{CES}		1,0	mA
栅极-发射极漏电流 Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{GES}		100	nA
开通延迟时间(电感负载) Turn-on delay time, inductive load	$I_C = 400\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 1,5\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{don}	0,20 0,22 0,23		μs μs μs
上升时间(电感负载) Rise time, inductive load	$I_C = 400\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 1,5\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_r	0,11 0,12 0,12		μs μs μs
关断延迟时间(电感负载) Turn-off delay time, inductive load	$I_C = 400\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 1,5\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{doff}	0,40 0,48 0,50		μs μs μs
下降时间(电感负载) Fall time, inductive load	$I_C = 400\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 1,5\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_f	0,07 0,10 0,11		μs μs μs
开通损耗能量(每脉冲) Turn-on energy loss per pulse	$I_C = 400\text{ A}, V_{CE} = 300\text{ V}, L_S = 35\text{ nH}$ $V_{GE} = \pm 15\text{ V}, di/dt = 2650\text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Gon} = 1,5\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{on}	8,75 13,0 13,5		mJ mJ mJ
关断损耗能量(每脉冲) Turn-off energy loss per pulse	$I_C = 400\text{ A}, V_{CE} = 300\text{ V}, L_S = 35\text{ nH}$ $V_{GE} = \pm 15\text{ V}, du/dt = 2300\text{ V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Goff} = 1,5\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{off}	18,0 26,0 28,5		mJ mJ mJ
短路数据 SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 800\text{ V}$ $V_{CE\text{max}} = V_{CES} - L_{SCE} \cdot di/dt$	$t_P \leq 10\ \mu\text{s}, T_{vj} = 25^{\circ}\text{C}$ $t_P \leq 10\ \mu\text{s}, T_{vj} = 150^{\circ}\text{C}$	I_{SC}	2200 1900		A A
结 - 外壳热阻 Thermal resistance, junction to case	每个 IGBT / per IGBT		R_{thJC}		0,07	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个 IGBT / per IGBT $\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$		R_{thCH}	0,046		K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{op}}$	-40	150	$^{\circ}\text{C}$

prepared by: MK	date of publication: 2013-11-11
approved by: MK	revision: 2.0

初步数据
Preliminary Data

二极管, D2 / D3 / Diode, D2 / D3
最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	650	V
连续正向直流电流 Continuous DC forward current		I_F	400	A
正向重复峰值电流 Repetitive peak forward current	$t_P = 1\text{ ms}$	I_{FRM}	800	A
I_{2t} -值 I_{2t} - value	$V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$ $V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I_{2t}	6700 6150	A^2s A^2s

特征值 / Characteristic Values

			min.	typ.	max.	
正向电压 Forward voltage	$I_F = 400\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 400\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 400\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	V_F	1,55 1,50 1,45	1,95	V V V
反向恢复峰值电流 Peak reverse recovery current	$I_F = 400\text{ A}, -di_F/dt = 2650\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 300\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	I_{RM}	145 205 215		A A A
恢复电荷 Recovered charge	$I_F = 400\text{ A}, -di_F/dt = 2650\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 300\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	Q_r	13,5 26,0 28,5		μC μC μC
反向恢复损耗 (每脉冲) Reverse recovery energy	$I_F = 400\text{ A}, -di_F/dt = 2650\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 300\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{rec}	3,40 6,35 7,15		mJ mJ mJ
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode		R_{thJC}		0,22	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个二极管 / per diode $\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$		R_{thCH}	0,077		K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{ op}}$	-40	150	$^{\circ}\text{C}$

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初步数据
Preliminary Data

IGBT, T2 / T3 / IGBT, T2 / T3

最大额定值 / Maximum Rated Values

集电极 - 发射极电压 Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	650	V
连续集电极直流电流 Continuous DC collector current	$T_C = 0^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	$I_{C\text{nom}}$ I_C	400 360	A A
集电极重复峰值电流 Repetitive peak collector current	$t_P = 1\text{ ms}$	I_{CRM}	800	A
总功率损耗 Total power dissipation	$T_C = 25^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	P_{tot}	880	W
栅极 - 发射极峰值电压 Gate-emitter peak voltage		V_{GES}	+/-20	V

特征值 / Characteristic Values

			min.	typ.	max.	
集电极 - 发射极饱和电压 Collector-emitter saturation voltage	$I_C = 400\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 400\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 400\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{sat}}$	1,75 2,00 2,10	2,15	V V V
栅极阈值电压 Gate threshold voltage	$I_C = 4,80\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		V_{GEth}	4,9	5,8	6,5 V
栅极电荷 Gate charge	$V_{GE} = -15\text{ V} \dots +15\text{ V}$		Q_G	3,20		μC
内部栅极电阻 Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		R_{Gint}	1,0		Ω
输入电容 Input capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{ies}	18,5		nF
反向传输电容 Reverse transfer capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{res}	0,57		nF
集电极-发射极截止电流 Collector-emitter cut-off current	$V_{CE} = 650\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{CES}		1,0	mA
栅极-发射极漏电流 Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{GES}		100	nA
开通延迟时间(电感负载) Turn-on delay time, inductive load	$I_C = 400\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 1,5\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{don}	0,08 0,10 0,10		μs μs μs
上升时间(电感负载) Rise time, inductive load	$I_C = 400\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 1,5\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_r	0,09 0,10 0,10		μs μs μs
关断延迟时间(电感负载) Turn-off delay time, inductive load	$I_C = 400\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 1,5\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{doff}	0,35 0,37 0,38		μs μs μs
下降时间(电感负载) Fall time, inductive load	$I_C = 400\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 1,5\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_f	0,08 0,11 0,11		μs μs μs
开通损耗能量(每脉冲) Turn-on energy loss per pulse	$I_C = 400\text{ A}, V_{CE} = 300\text{ V}, L_S = 35\text{ nH}$ $V_{GE} = \pm 15\text{ V}, di/dt = 3300\text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Gon} = 1,5\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{on}	6,30 9,40 11,0		mJ mJ mJ
关断损耗能量(每脉冲) Turn-off energy loss per pulse	$I_C = 400\text{ A}, V_{CE} = 300\text{ V}, L_S = 35\text{ nH}$ $V_{GE} = \pm 15\text{ V}, du/dt = 3350\text{ V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Goff} = 1,5\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{off}	20,0 23,5 24,5		mJ mJ mJ
短路数据 SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 360\text{ V}$ $V_{CEmax} = V_{CES} - L_{SCE} \cdot di/dt$	$t_P \leq 10\ \mu\text{s}, T_{vj} = 25^{\circ}\text{C}$ $t_P \leq 10\ \mu\text{s}, T_{vj} = 150^{\circ}\text{C}$	I_{SC}	1800 1400		A A
结 - 外壳热阻 Thermal resistance, junction to case	每个 IGBT / per IGBT		R_{thJC}		0,17	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个 IGBT / per IGBT $\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$		R_{thCH}	0,074		K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{op}}$	-40	150	$^{\circ}\text{C}$

prepared by: MK	date of publication: 2013-11-11
approved by: MK	revision: 2.0



初步数据
Preliminary Data

二极管, D1 / D4 / Diode, D1 / D4
最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1200	V
连续正向直流电流 Continuous DC forward current		I_F	400	A
正向重复峰值电流 Repetitive peak forward current	$t_P = 1\text{ ms}$	I_{FRM}	800	A
I ² t-值 I ² t - value	$V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$ $V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I^2t	15500 11500	A ² s A ² s

特征值 / Characteristic Values

			min.	typ.	max.	
正向电压 Forward voltage	$I_F = 400\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 400\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 400\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	V_F	1,80 1,85 1,90	2,30	V V V
反向恢复峰值电流 Peak reverse recovery current	$I_F = 400\text{ A}, -di_F/dt = 3300\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 300\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	I_{RM}	255 310 325		A A A
恢复电荷 Recovered charge	$I_F = 400\text{ A}, -di_F/dt = 3300\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 300\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	Q_r	29,0 56,0 65,0		μC μC μC
反向恢复损耗 (每脉冲) Reverse recovery energy	$I_F = 400\text{ A}, -di_F/dt = 3300\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 300\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{rec}	8,70 16,5 19,0		mJ mJ mJ
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode		R_{thJC}		0,16	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个二极管 / per diode $\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$		R_{thCH}	0,056		K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{ op}}$	-40	150	$^{\circ}\text{C}$

负温度系数热敏电阻 / NTC-Thermistor

特征值 / Characteristic Values

			min.	typ.	max.	
额定电阻值 Rated resistance	$T_C = 25^{\circ}\text{C}$	R_{25}		5,00		k Ω
R100 偏差 Deviation of R100	$T_C = 100^{\circ}\text{C}, R_{100} = 493\ \Omega$	$\Delta R/R$	-5		5	%
耗散功率 Power dissipation	$T_C = 25^{\circ}\text{C}$	P_{25}			20,0	mW
B-值 B-value	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/50}$		3375		K
B-值 B-value	$R_2 = R_{25} \exp [B_{25/80}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/80}$		3411		K
B-值 B-value	$R_2 = R_{25} \exp [B_{25/100}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/100}$		3433		K

根据应用手册标定

Specification according to the valid application note.

prepared by: MK	date of publication: 2013-11-11
approved by: MK	revision: 2.0



初步数据
Preliminary Data

模块 / Module

绝缘测试电压 Isolation test voltage	RMS, f = 50 Hz, t = 1 min.	V _{ISOL}	2,5		kV
模块基板材料 Material of module baseplate			Cu		
内部绝缘 Internal isolation	基本绝缘 (class 1, IEC 61140) basic insulation (class 1, IEC 61140)		Al ₂ O ₃		
爬电距离 Creepage distance	端子- 散热片 / terminal to heatsink 端子- 端子 / terminal to terminal		25,0 12,5		mm
电气间隙 Clearance	端子- 散热片 / terminal to heatsink 端子- 端子 / terminal to terminal		11,0 7,0		mm
相对电痕指数 Comperative tracking index		CTI	> 200		
			min.	typ.	max.
杂散电感, 模块 Stray inductance module		L _{sCE}	38		nH
模块引线电阻, 端子-芯片 Module lead resistance, terminals - chip	T _c = 25°C, 每个开关 / per switch	R _{CC+EE'}	0,75		mΩ
储存温度 Storage temperature		T _{stg}	-40	125	°C
模块安装的安装扭矩 Mounting torque for modul mounting	螺丝 M5 根据相应的应用手册进行安装 Screw M5 - Mounting according to valid application note	M	3,00	-	6,00 Nm
端子联接扭矩 Terminal connection torque	螺丝 M6 根据相应的应用手册进行安装 Screw M6 - Mounting according to valid application note	M	3,0	-	6,0 Nm
重量 Weight		G	400		g

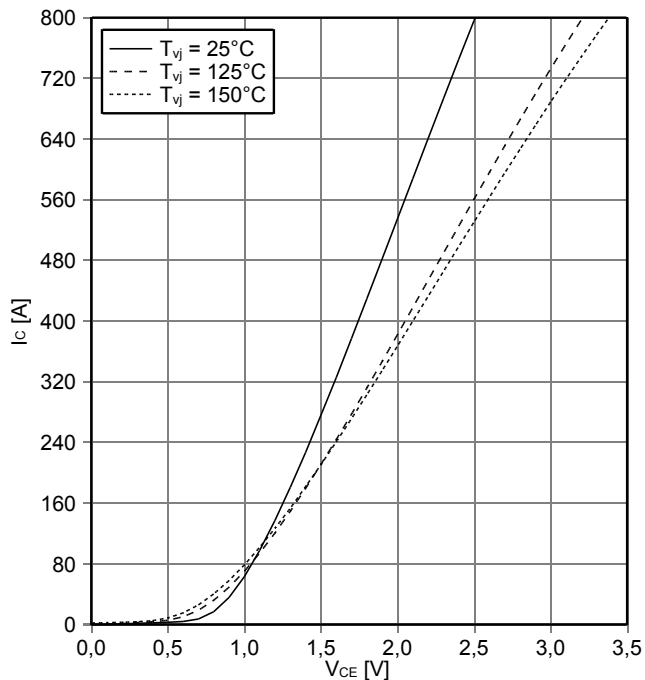
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初步数据
Preliminary Data

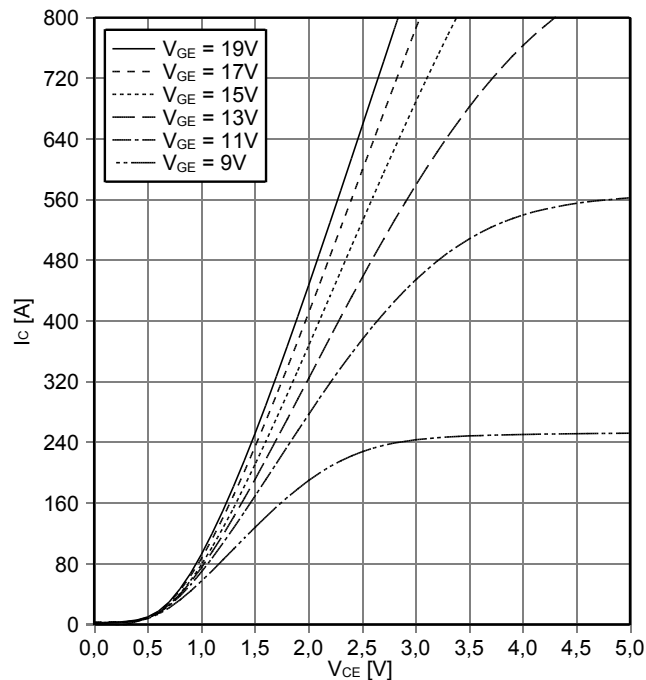
输出特性 IGBT, T1 / T4 (典型)
output characteristic IGBT, T1 / T4 (typical)

$I_C = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



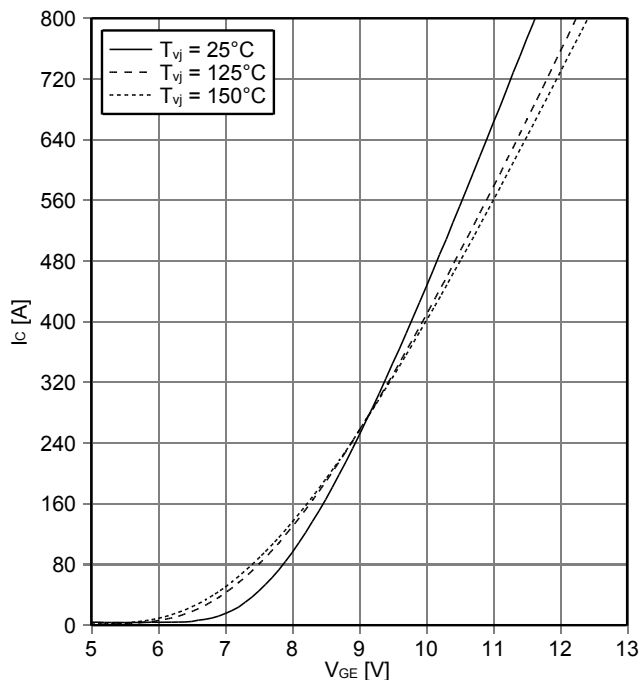
输出特性 IGBT, T1 / T4 (典型)
output characteristic IGBT, T1 / T4 (typical)

$I_C = f(V_{CE})$
 $T_{vj} = 150^\circ\text{C}$



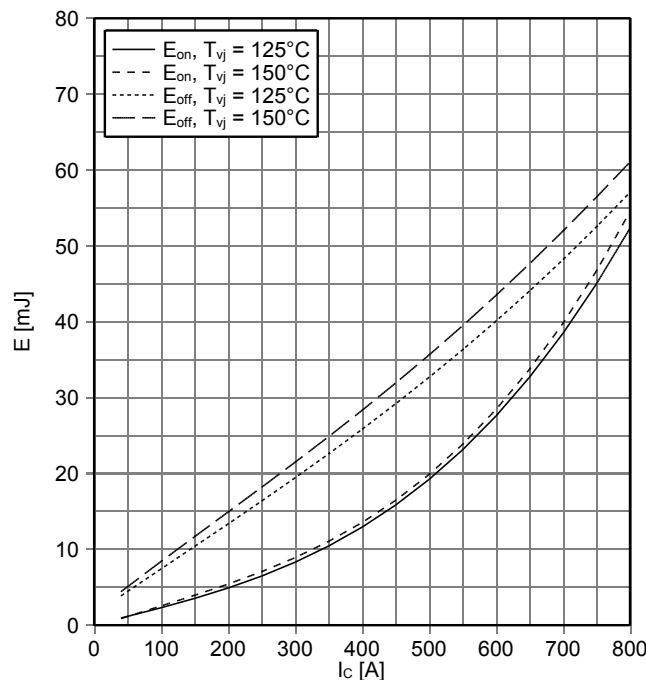
传输特性 IGBT, T1 / T4 (典型)
transfer characteristic IGBT, T1 / T4 (typical)

$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



开关损耗 IGBT, T1 / T4 (典型)
switching losses IGBT, T1 / T4 (typical)

$E_{on} = f(I_C), E_{off} = f(I_C)$
 $V_{GE} = \pm 15\text{ V}, R_{Gon} = 1.5\ \Omega, R_{Goff} = 1.5\ \Omega, V_{CE} = 300\text{ V}$

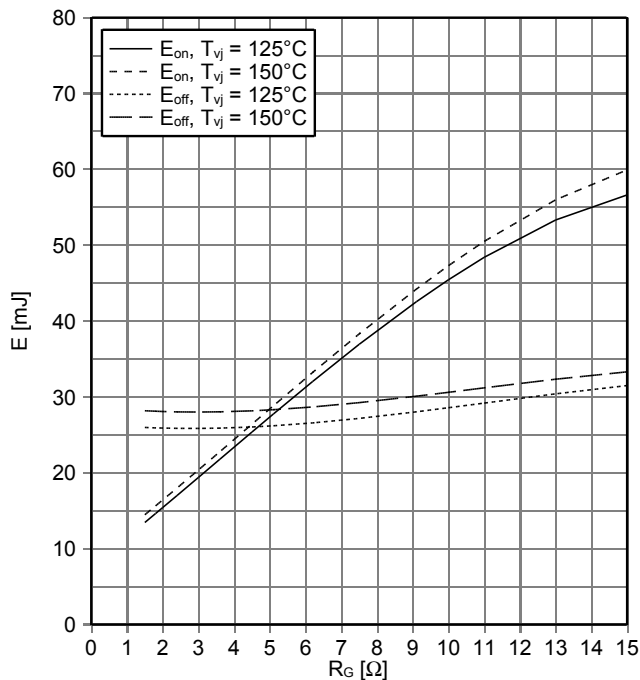


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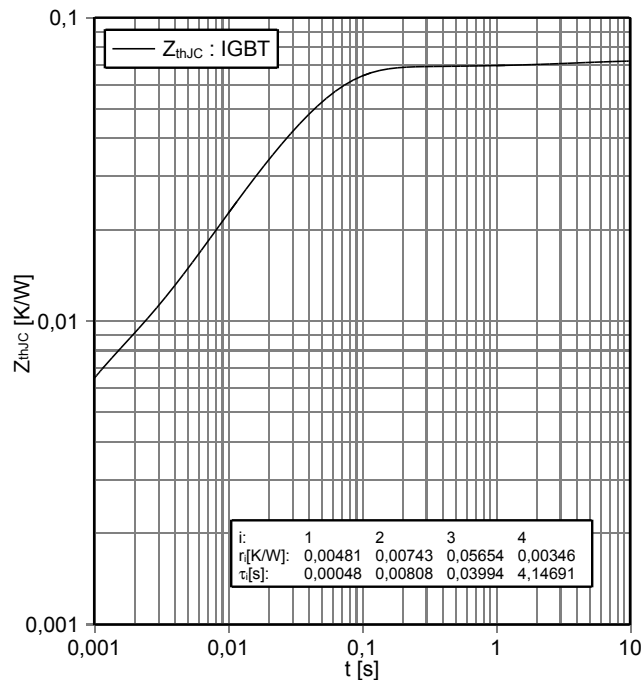
开关损耗 IGBT, T1 / T4 (典型)
switching losses IGBT, T1 / T4 (typical)

$E_{on} = f(R_G)$, $E_{off} = f(R_G)$
 $V_{GE} = \pm 15\text{ V}$, $I_C = 400\text{ A}$, $V_{CE} = 300\text{ V}$



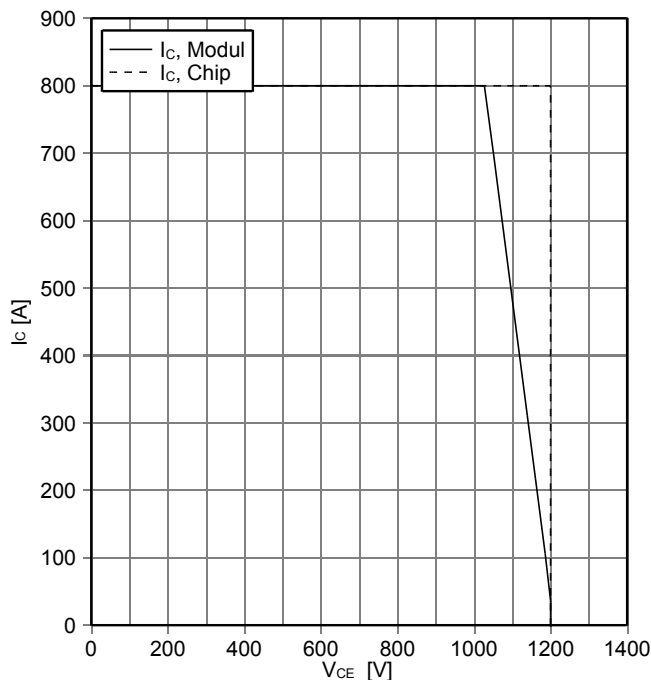
瞬态热阻抗 IGBT, T1 / T4
transient thermal impedance IGBT, T1 / T4

$Z_{thJC} = f(t)$



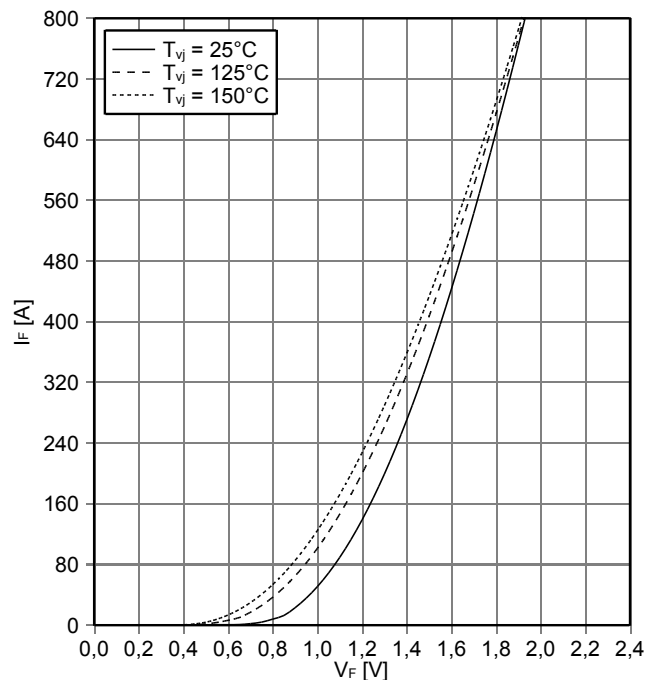
反偏安全工作区 IGBT, T1 / T4 (RBSOA)
reverse bias safe operating area IGBT, T1 / T4 (RBSOA)

$I_C = f(V_{CE})$
 $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 1.5\ \Omega$, $T_{vj} = 150^\circ\text{C}$



正向偏压特性 二极管, D2 / D3 (典型)
forward characteristic of Diode, D2 / D3 (typical)

$I_F = f(V_F)$

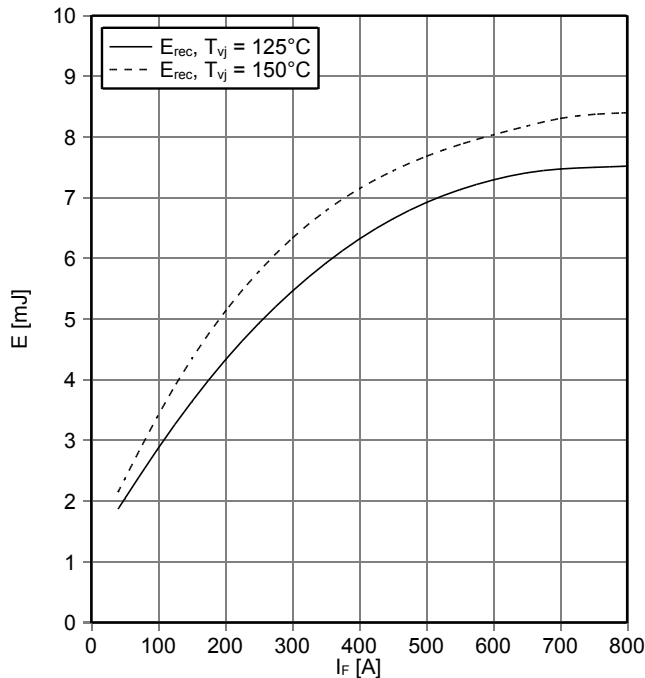


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初步数据
Preliminary Data

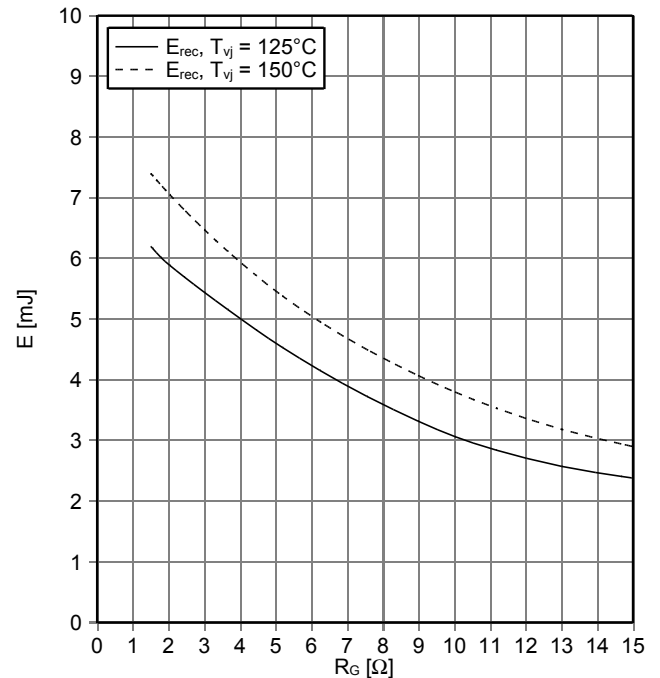
开关损耗 二极管, D2 / D3 (典型)
switching losses Diode, D2 / D3 (typical)

$E_{rec} = f(I_F)$
 $R_{Gon} = 1.5 \Omega, V_{CE} = 300 V$



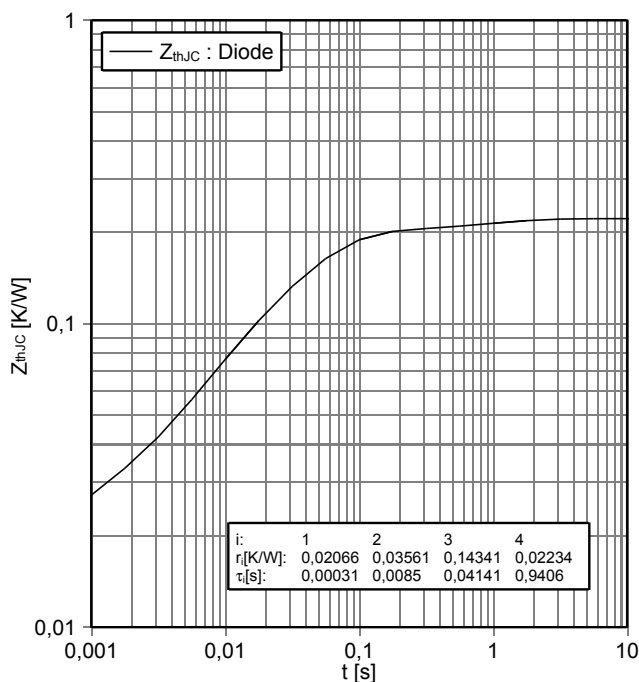
开关损耗 二极管, D2 / D3 (典型)
switching losses Diode, D2 / D3 (typical)

$E_{rec} = f(R_G)$
 $I_F = 400 A, V_{CE} = 300 V$



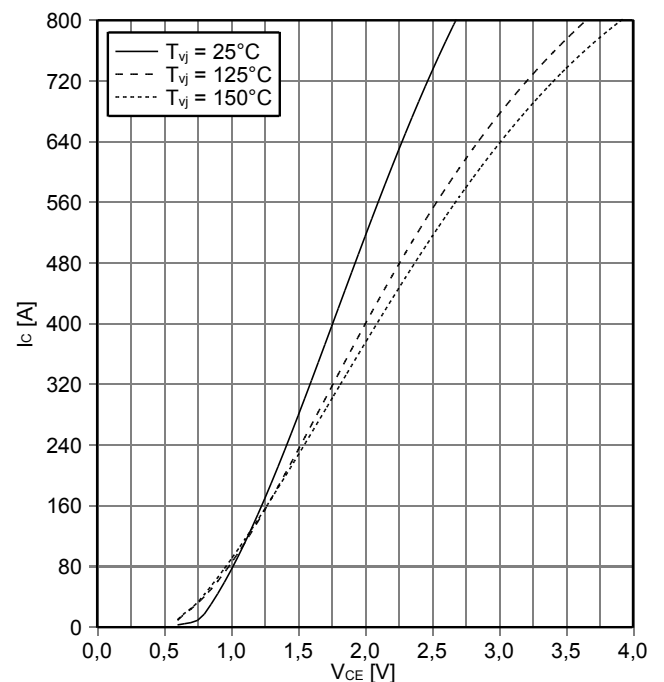
瞬态热阻抗 二极管, D2 / D3
transient thermal impedance Diode, D2 / D3

$Z_{thJC} = f(t)$



输出特性 IGBT, T2 / T3 (典型)
output characteristic IGBT, T2 / T3 (typical)

$I_C = f(V_{CE})$
 $V_{GE} = 15 V$



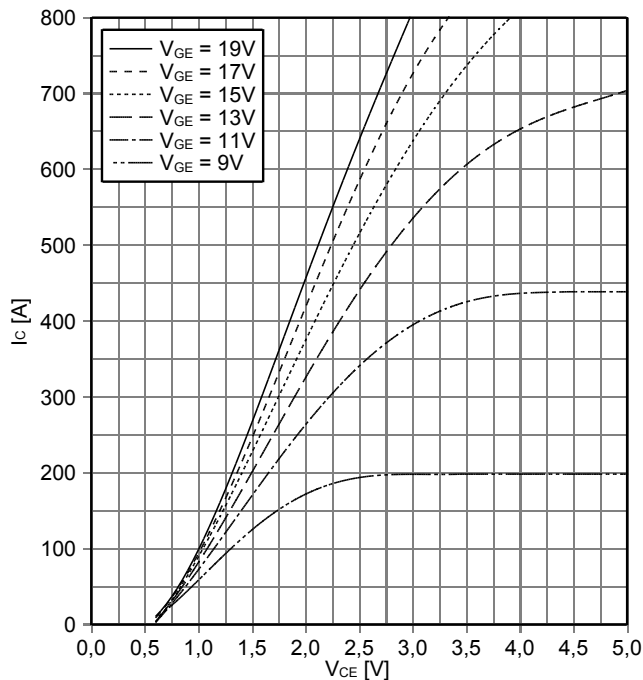
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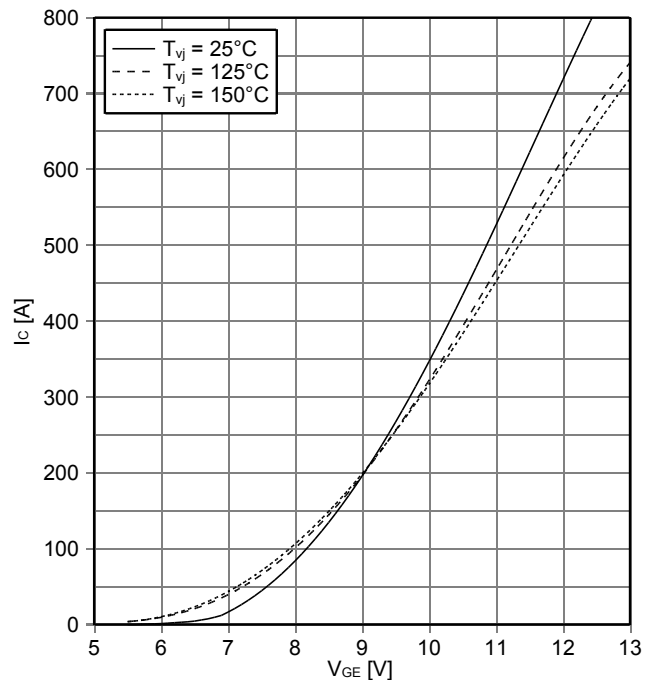
输出特性 IGBT, T2 / T3 (典型)
output characteristic IGBT, T2 / T3 (typical)

$I_C = f(V_{CE})$
 $T_{vj} = 150^\circ\text{C}$



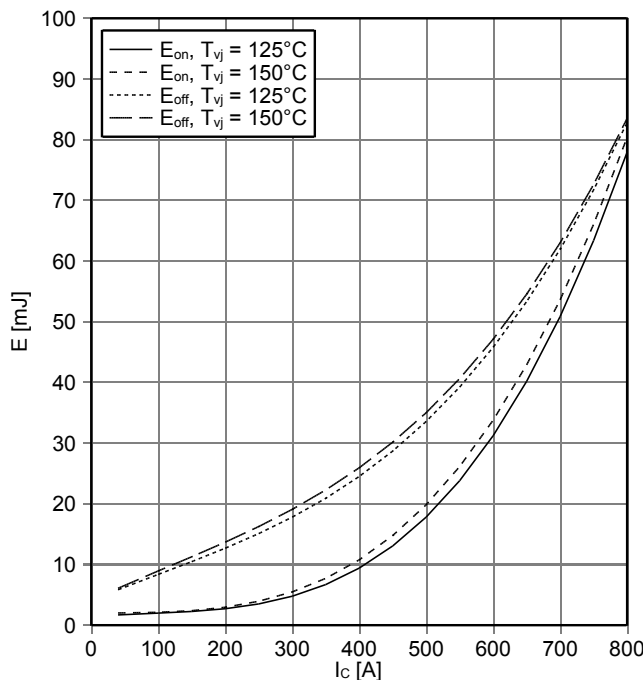
传输特性 IGBT, T2 / T3 (典型)
transfer characteristic IGBT, T2 / T3 (typical)

$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



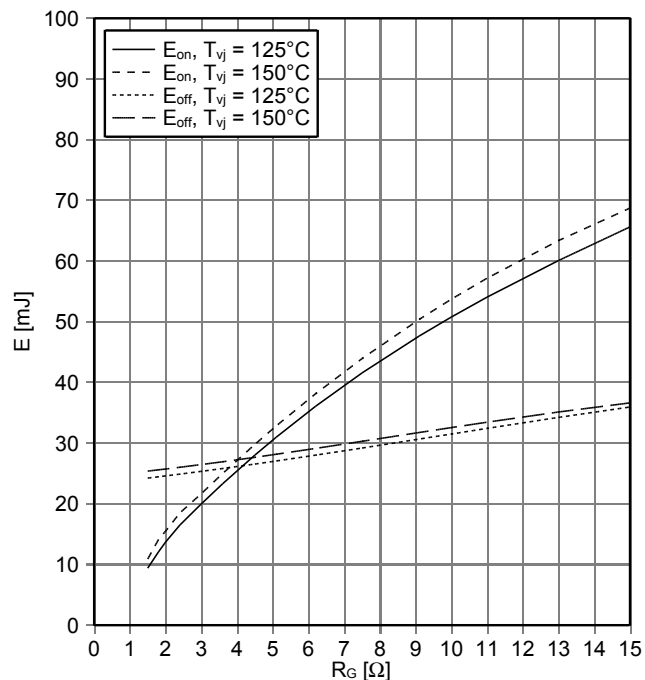
开关损耗 IGBT, T2 / T3 (典型)
switching losses IGBT, T2 / T3 (typical)

$E_{on} = f(I_C), E_{off} = f(I_C)$
 $V_{GE} = \pm 15\text{ V}, R_{Gon} = 1.5\ \Omega, R_{Goff} = 1.5\ \Omega, V_{CE} = 300\text{ V}$



开关损耗 IGBT, T2 / T3 (典型)
switching losses IGBT, T2 / T3 (typical)

$E_{on} = f(R_G), E_{off} = f(R_G)$
 $V_{GE} = \pm 15\text{ V}, I_C = 400\text{ A}, V_{CE} = 300\text{ V}$

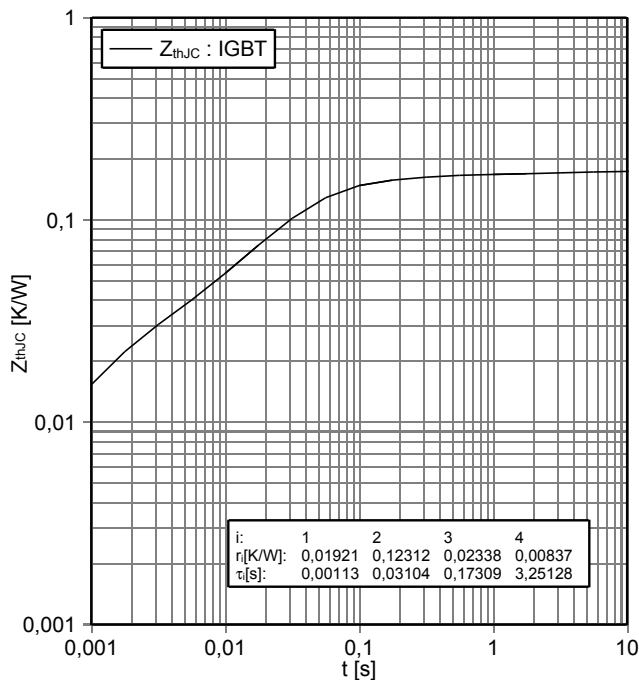


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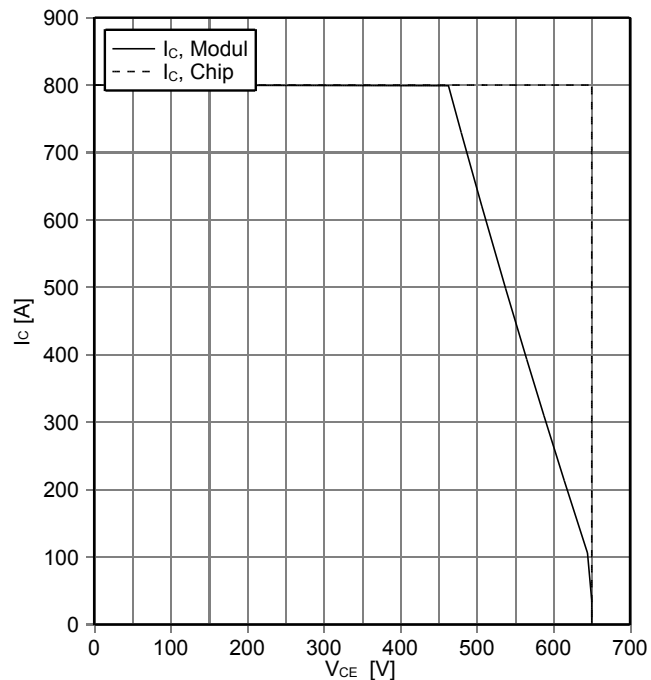


初步数据
Preliminary Data

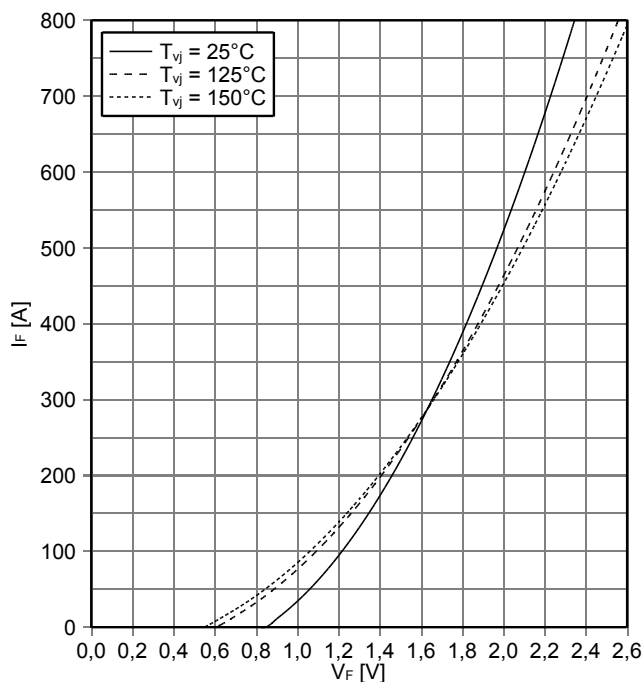
瞬态热阻抗 IGBT, T2 / T3
transient thermal impedance IGBT, T2 / T3
 $Z_{thJC} = f(t)$



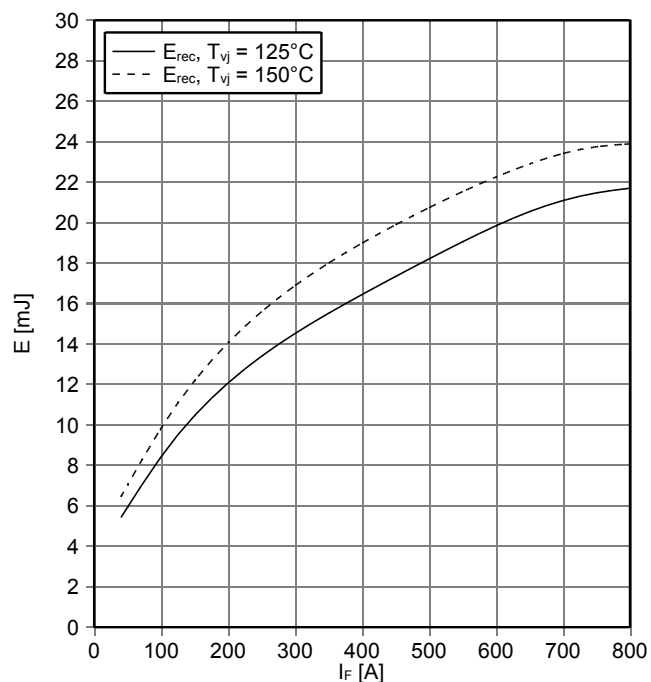
反偏安全工作区 IGBT, T2 / T3 (RBSOA)
reverse bias safe operating area IGBT, T2 / T3 (RBSOA)
 $I_C = f(V_{CE})$
 $V_{GE} = \pm 15 V, R_{Goff} = 1.5 \Omega, T_{vj} = 150^\circ C$



正向偏压特性 二极管, D1 / D4 (典型)
forward characteristic of Diode, D1 / D4 (typical)
 $I_F = f(V_F)$



开关损耗 二极管, D1 / D4 (典型)
switching losses Diode, D1 / D4 (typical)
 $E_{rec} = f(I_F)$
 $R_{Gon} = 1.5 \Omega, V_{CE} = 300 V$



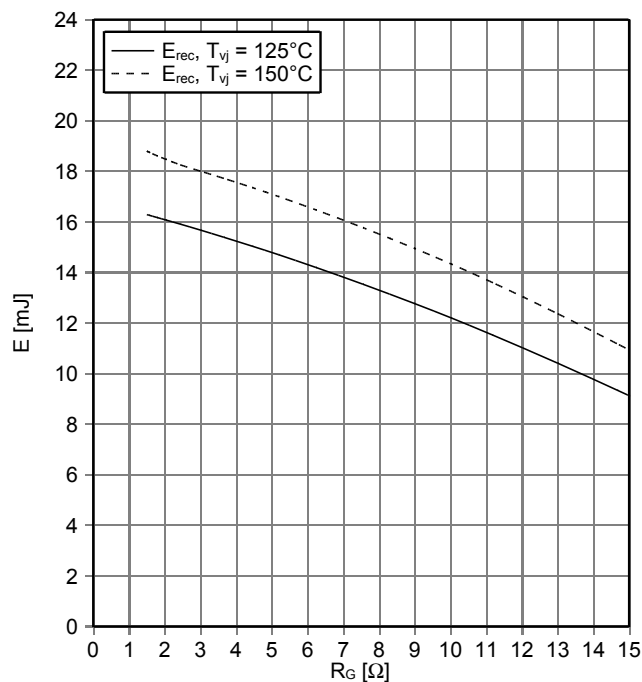
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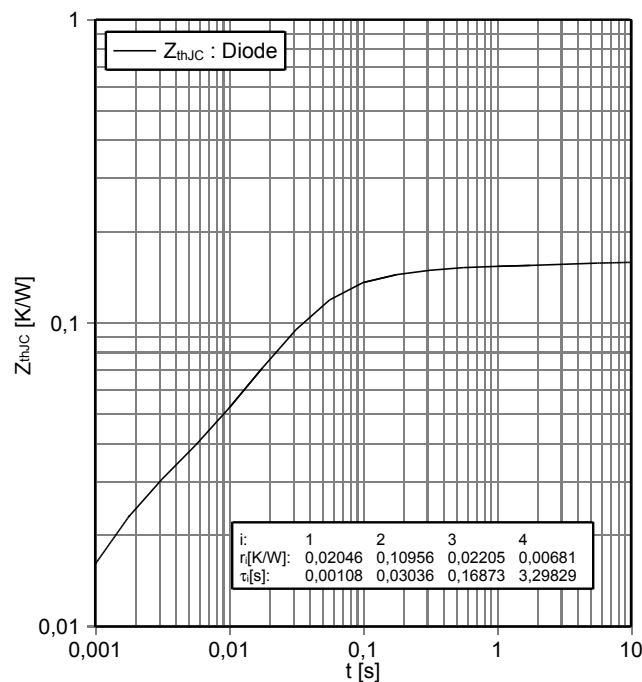
开关损耗 二极管, D1 / D4 (典型)
switching losses Diode, D1 / D4 (typical)

$E_{rec} = f(R_G)$
 $I_F = 400\text{ A}, V_{CE} = 300\text{ V}$



瞬态热阻抗 二极管, D1 / D4
transient thermal impedance Diode, D1 / D4

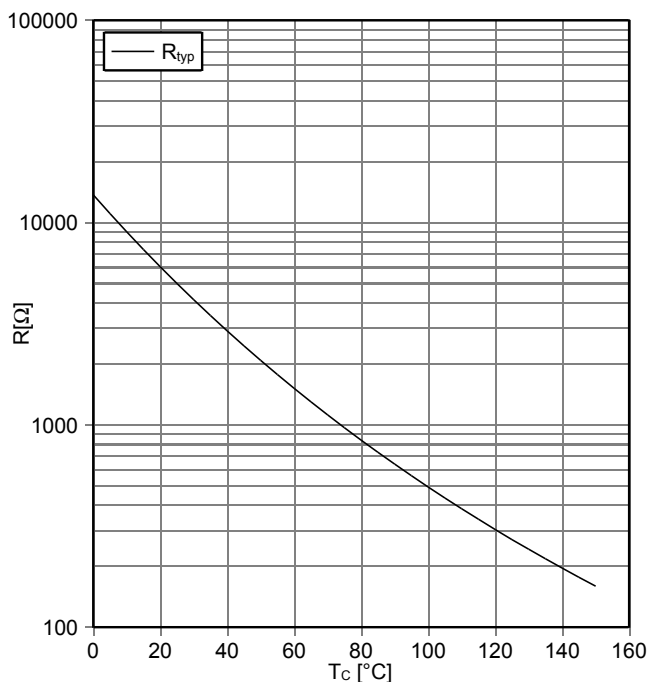
$Z_{thJC} = f(t)$



i:	1	2	3	4
r _i [K/W]:	0,02046	0,10956	0,02205	0,00681
τ _i [s]:	0,00108	0,03036	0,16873	3,29829

负温度系数热敏电阻 温度特性
NTC-Thermistor-temperature characteristic (typical)

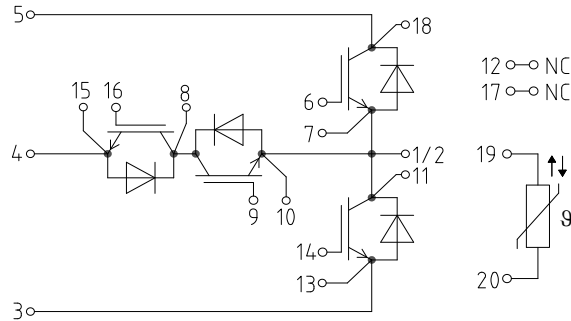
$R = f(T)$



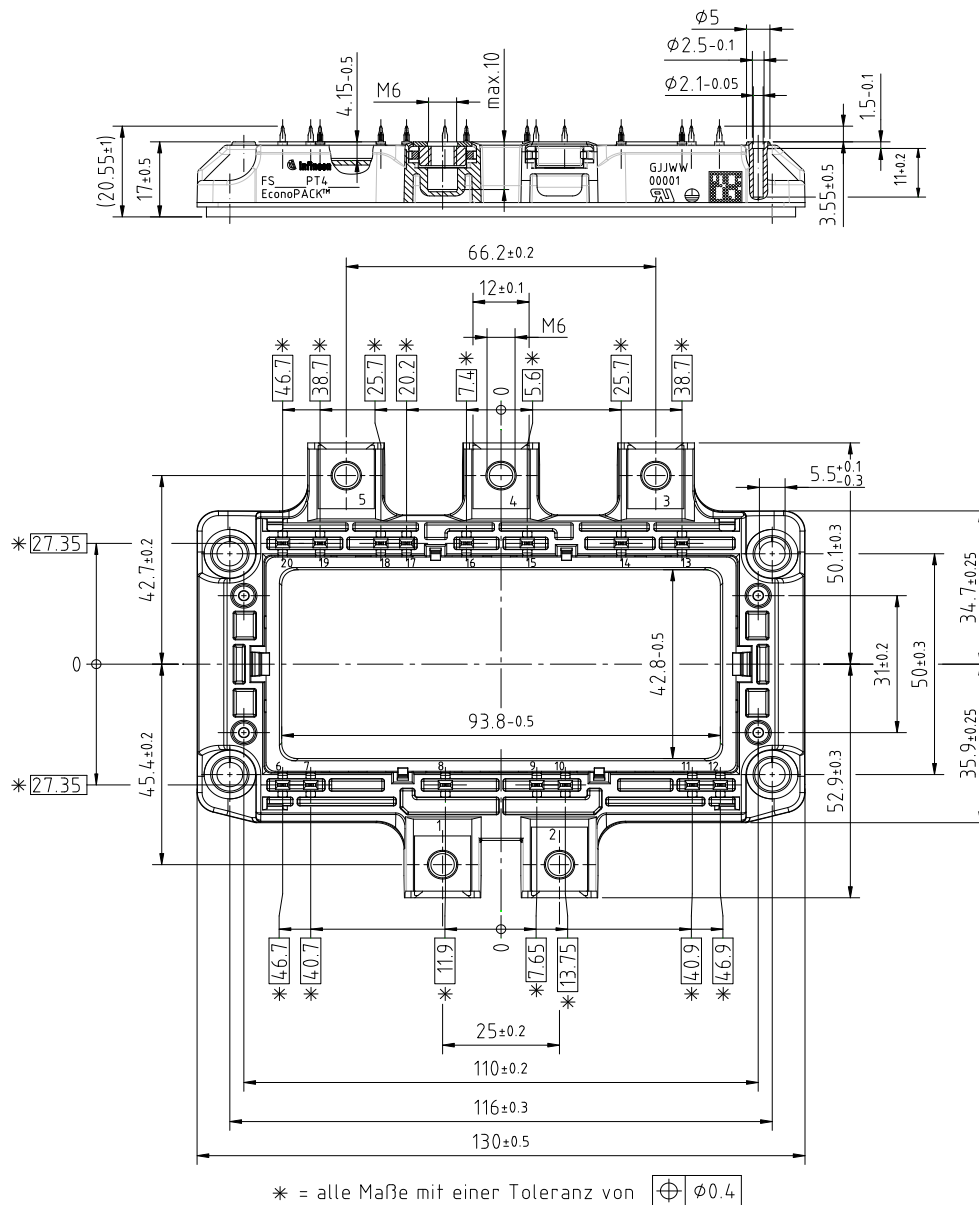
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初步数据
Preliminary Data

接线图 / circuit_diagram_headline



封装尺寸 / package outlines



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**初步数据
Preliminary Data**

使用条件和条款

使用条件和条款

产品规格书中的数据是专门为技术人员提供的，您和您的技术部门应该针对您的应用来评估产品及产品的所有参数是否适合

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请注意，对这类应用我们强烈建议

-执行联合的风险和质量评估

-得到质量协议的结论

-建立联合的测试和出厂产品检查，我们可以根据测试的实际情况供货

如果有必要，请根据实际需要将类似的说明给你的客户

保留产品规格书的修改权

Terms & Conditions of usage

The data contained in this product data sheet is exclusively intended for technically trained staff. You and your technical departments will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to such application.

This product data sheet is describing the characteristics of this product for which a warranty is granted. Any such warranty is granted exclusively pursuant the terms and conditions of the supply agreement. There will be no guarantee of any kind for the product and its characteristics. The information in the valid application- and assembly notes of the module must be considered.

Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of our product, please contact the sales office, which is responsible for you (see www.infineon.com). For those that are specifically interested we may provide application notes.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact the sales office, which is responsible for you.

Should you intend to use the Product in aviation applications, in health or live endangering or life support applications, please notify. Please note, that for any such applications we urgently recommend

- to perform joint Risk and Quality Assessments;

- the conclusion of Quality Agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery depended on the realization of any such measures.

If and to the extent necessary, please forward equivalent notices to your customers.

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Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.